UF2815B



RF Power MOSFET Transistor 15W, 100-500 MHz, 28V

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Features

- N-Channel enhancement mode device
- DMOS structure
- · Lower capacitances for broadband operation
- · Common source configuration
- Lower noise floor
- RoHS Compliant
- 100 MHz to 500 MHz operation

ABSOLUTE MAXIMUM RATINGS AT 25° C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V_{GS}	20	V
Drain-Source Current	I _{DS}	4.2	Α
Power Dissipation	P _D	48.6	W
Junction Temperature	TJ	200	°C
Storage Temperature	T _{STG}	-55 to 150	°C
Thermal Resistance	θ_{JC}	3.6	°C/W

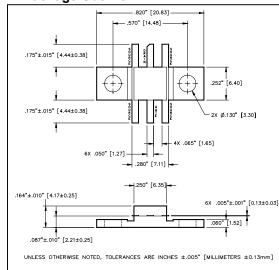
TYPICAL DEVICE IMPEDANCES

F (MHz)	Z _{IN} (Ω)	Z _{LOAD} (Ω)		
100	6.4-j25.0	22.0+j16.0		
300	6.5-j12.0	15.0+j14.0		
500	1.7-j10.5 8.0=j10.5			
V_{DD} =28V, I_{DQ} =150 mA, P_{OUT} =15.0 W				

 Z_{IN} is the series equivalent input impedance of the device from gate to source.

 Z_{LOAD} is the optimum series equivalent load impedance as measured from drain to ground.

Package Outline



LETTER	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	20.70	20.96	.815	.825
В	14.35	14.61	.565	.575
С	14.73	15.24	.580	.575
D	6.27	6.53	.247	.257
Е	6.22	6.48	.245	.255
F	1.14	1.40	.045	.055
G	1.52	1.78	.060	.070
Н	2.92	3.17	.115	.125
J	1.40	1.65	.055	.065
K	2.03	2.39	.080	.094
L	3.66	4.32	.144	.170
М	.10	.15	.004	.006

ELECTRICAL CHARACTERISTICS AT 25°C

Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	65	-	V	V _{GS} = 0.0 V , I _{DS} = 6.0 mA
Drain-Source Leakage Current	I _{DSS}	-	3.0	mA	V _{GS} = 28.0 V , V _{GS} = 0.0 V
Gate-Source Leakage Current	I _{GSS}	-	3.0	μA	V _{GS} = 20.0 V , V _{DS} = 0.0 V
Gate Threshold Voltage	$V_{GS(TH)}$	2.0	6.0	V	V _{DS} = 10.0 V , I _{DS} = 30.0 mA
Forward Transconductance	G _M	.240	-	S	V_{DS} = 10.0 V , I_{DS} 300.0 mA , Δ V_{GS} = 1.0V, 80 μ s Pulse
Input Capacitance	C _{ISS}	-	21	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Output Capacitance	Coss	-	15	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Reverse Capacitance	C _{RSS}	-	7.2	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Power Gain	G _P	10	-	dB	V _{DD} = 28.0 V, I _{DQ} = 150.0 mA, P _{OUT} = 15.0 W F =500 MHz
Drain Efficiency	η _D	50	-	%	V _{DD} = 28.0 V, I _{DQ} = 150.0 mA, P _{OUT} = 15.0 W F =500 MHz
Load Mismatch Tolerance	VSWR-T	-	20:1	-	V _{DD} = 28.0 V, I _{DQ} = 150.0 mA, P _{OUT} = 15.0 W F =500 MHz

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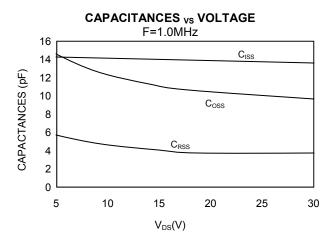
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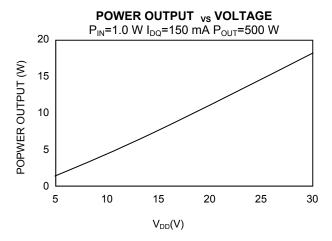


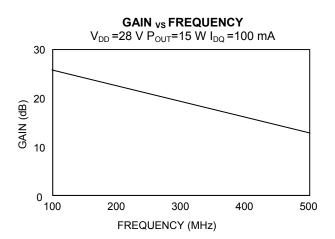
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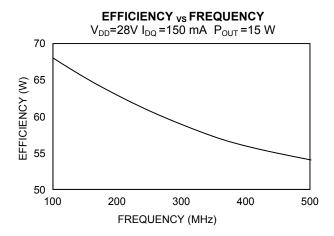
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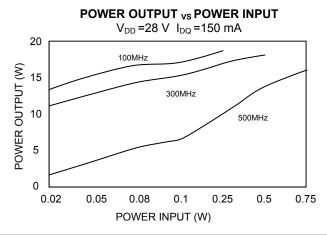
Typical Broadband Performance Curves











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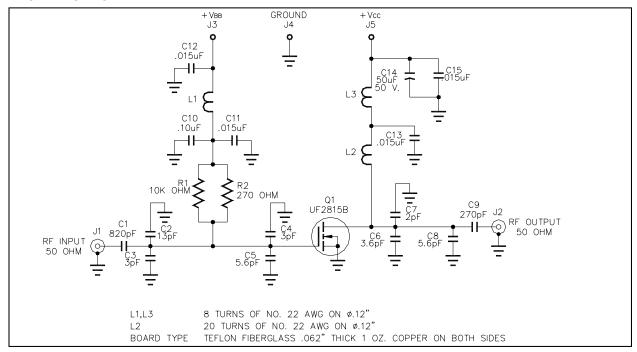
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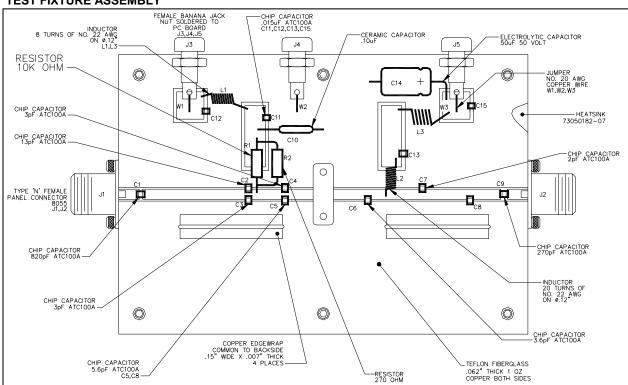
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TEST FIXTURE SCHEMATIC



TEST FIXTURE ASSEMBLY



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